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Docket: 0756-1614

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Continuation Application of )  
Takeshi FUKUNAGA et al. )  
Based On Serial No. 08/519,420 ) Art Unit: 1112  
Which Was Filed: August 25, 1995 ) Examiner: M. Padgett  
For: METHOD OF MANUFACTURING )  
A SEMICONDUCTOR DEVICE ) Date: December 30, 1996

PRELIMINARY AMENDMENT

Honorable Assistant Commissioner for Patents  
Washington, D.C. 20231

Sir:

Please preliminarily amend the subject application as follows:

IN THE CLAIMS:

Please amend claims 1 and 2 as follows:

1. (Three Times Amended) A method for manufacturing a semiconductor device, comprising the steps of:  
irradiating a non-single crystalline silicon film with laser light,  
to crystallize the non-single crystalline silicon film;  
thermally annealing the non-single crystalline silicon film in the temperature range of 450-750°C [under a nitrogen atmosphere] to decrease a